Product Highlights

- **AEC-Q100 Qualification for /V Devices**
- Reinforced Galvanic Isolation for Digital Signals
  - 16 Wide SOIC with 8mm Creepage and Clearance
  - Withstands $5kV_{RMS}$ for 60s (V_{ISO})
  - Continuously Withstands $848V_{RMS}$ (V_{IOWM})
  - Withstands ±12.8kV Surge between GNDA and GNDB with 1.2/50µs Waveform
  - High CMTI (50kV/µs, typ)
- Low Power Consumption
  - 0.71mW per Channel at 1Mbps with V_{DD} = 1.8V
  - 1.34mW per Channel at 1Mbps with V_{DD} = 3.3V
  - 3.21mW per Channel at 100Mbps with V_{DD} = 1.8V
- Low Propagation Delay and Low Jitter
  - Maximum Data Rate Up to 200Mbps
  - Low Propagation Delay 7ns (typ) at V_{DD} = 3.3V
  - Clock Jitter RMS 11.1ps (typ)
- *Safety Regulatory Approvals*
  - UL According to UL1577
  - cUL According to CSA Bulletin 5A
  - VDE 0884-11 Reinforced Insulation (Pending)

Key Applications

- Automotive
  - Hybrid Electric Vehicle
  - Chargers
  - Battery Management System (BMS)
 - Inverters

The MAX22663−MAX22666 are a family of 6-channel, reinforced, fast, low-power digital galvanic isolators using Analog Devices' proprietary process technology. All devices feature reinforced isolation with a withstand voltage rating of $5kV_{RMS}$ for 60 seconds. Both automotive and general-purpose devices are rated for operation at ambient temperatures from -40°C to +125°C.

Devices with /V suffix are AEC-Q100 qualified. See the *Ordering Information* for all automotive grade part numbers.

- Industrial
  - Isolated SPI, RS-232/422/485, CAN, Digital I/O
  - Fieldbus Communications
  - Motor Control
  - Medical Systems

These devices transfer digital signals between circuits with different power domains, using as little as 0.71mW per channel at 1Mbps (1.8V supply). The low-power feature reduces system dissipation, increases reliability, and enables compact designs.

Simplified Application Diagram
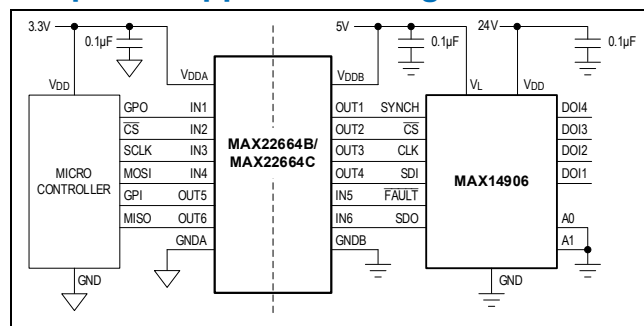
Pin Description
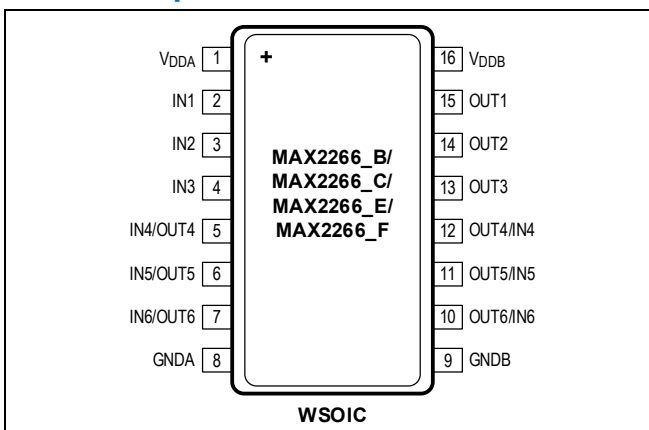
Devices are available with a maximum data rate of either 25Mbps or 200Mbps and with default-high or default-low outputs. The devices feature low propagation delay and low clock jitter, reducing system latency.

Independent 1.71V to 5.5V supplies on each side also make the devices suitable for use as level translators.

Three channels of the MAX22663 transmit digital signals in one direction, while the remaining three do in the opposite. The MAX22664 provides four channels for digital signal transmission, two of which travel in one direction and the other two in the opposite direction. The MAX22665 provides five channels for digital signal transmission in one direction and the other in the opposite direction. The MAX22666 features all six channels transmitting digital signals in one direction.

Ordering Information ***appears at end of the data sheet***

Absolute Maximum Ratings

V_{DDA} to GNDA ....-0.3V to +6V

V_{DDB} to GNDB ....-0.3V to +6V

IN_ on Side A to GNDA ....-0.3V to +6V

IN_ on Side B to GNDB ....-0.3V to +6V

OUT_ on Side A to GNDA ....-0.3V to (V_{DDA} + 0.3V)

OUT_ on Side B to GNDB ....-0.3V to (V_{DDB} + 0.3V)

Short-Circuit Continuous Current

   OUT_ on Side A to GNDA .... ±30mA

OUT_ on Side B to GNDB...±30mA

Continuous Power Dissipation (T_A = +70°C)

   Wide SOIC (derate 14.95mW/°C above +70°C) 1195.81mW

Temperature Ratings

   Operating Temperature Range ....-40°C to +125°C

   Maximum Junction Temperature.............................+150°C

   Storage Temperature Range......................-60°C to +150°C

   Lead Temperature (soldering, 10s).........................+300°C

   Soldering Temperature (reflow)...............................+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

PACKAGE TYPE: 16 WIDE SOIC	
Package Code	W16MS+13
Outline Number	*21-0042*
Land Pattern Number	*90-0107*
THERMAL RESISTANCE, FOUR LAYER BOARD:	
Junction-to-Ambient (θ_{JA})	66.90°C/W
Junction-to-Case Thermal Resistance (θ_{JC})	42.50°C/W

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to *http://www.maximintegrated.com/thermal-tutorial*.

For the latest package outline information and land patterns (footprints), go to *http://www.maximintegrated.com/packages*. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Reinforced, Fast, Low-Power, Six-Channel Digital Isolators

DC Electrical Characteristics

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 1*, *Note 3*))

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
SUPPLY VOLTAGE							
Supply Voltage	V_{DDA}	Relative to GNDA		1.71		5.5	V
	V_{DDB}	Relative to GNDB		1.71		5.5	
Undervoltage-Lockout Threshold	$V_{UVLO\_}$	$V_{DD\_}$ rising		1.5	1.6	1.66	V
Undervoltage-Lockout Threshold Hysteresis	V_{UVLO_HYST}				45		mV
MAX22663 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		1.23	2.28	mA
			V_{DDA} = 3.3V		1.22	2.25	
			V_{DDA} = 2.5V		1.21	2.24	
			V_{DDA} = 1.8V		1.18	1.97	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		7.83	10.26	
			V_{DDA} = 3.3V		6.47	8.71	
			V_{DDA} = 2.5V		5.90	8.03	
			V_{DDA} = 1.8V		5.35	7.10	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		1.23	2.28	mA
			V_{DDB} = 3.3V		1.22	2.25	
			V_{DDB} = 2.5V		1.21	2.24	
			V_{DDB} = 1.8V		1.18	1.97	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		7.83	10.26	
			V_{DDB} = 3.3V		6.47	8.71	
			V_{DDB} = 2.5V		5.90	8.03	
			V_{DDB} = 1.8V		5.35	7.10	
MAX22664 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		1.09	2.01	mA
			V_{DDA} = 3.3V		1.07	1.99	
			V_{DDA} = 2.5V		1.06	1.98	
			V_{DDA} = 1.8V		1.04	1.66	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		7.63	10.10	
			V_{DDA} = 3.3V		6.67	9.01	
			V_{DDA} = 2.5V		6.28	8.52	
			V_{DDA} = 1.8V		5.84	7.67	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		1.38	2.55	mA
			V_{DDB} = 3.3V		1.36	2.52	
			V_{DDB} = 2.5V		1.35	2.51	
			V_{DDB} = 1.8V		1.32	2.28	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		8.04	10.38	
			V_{DDB} = 3.3V		6.27	8.41	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 1*, *Note 3*))

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
			V_{DDB} = 2.5V		5.54	7.53	
			V_{DDB} = 1.8V		4.87	6.53	
MAX22665 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		0.94	1.74	mA
			V_{DDA} = 3.3V		0.93	1.72	
			V_{DDA} = 2.5V		0.92	1.71	
			V_{DDA} = 1.8V		0.90	1.34	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		7.44	9.96	
			V_{DDA} = 3.3V		6.88	9.31	
			V_{DDA} = 2.5V		6.64	9.03	
			V_{DDA} = 1.8V		6.32	8.23	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		1.53	2.82	mA
			V_{DDB} = 3.3V		1.50	2.79	
			V_{DDB} = 2.5V		1.50	2.78	
			V_{DDB} = 1.8V		1.45	2.59	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		8.36	10.64	
			V_{DDB} = 3.3V		6.16	8.19	
			V_{DDB} = 2.5V		5.24	7.10	
			V_{DDB} = 1.8V		4.45	6.01	
MAX22666 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		0.79	1.47	mA
			V_{DDA} = 3.3V		0.78	1.45	
			V_{DDA} = 2.5V		0.78	1.44	
			V_{DDA} = 1.8V		0.75	1.02	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		7.25	9.81	
			V_{DDA} = 3.3V		7.08	9.61	
			V_{DDA} = 2.5V		7.00	9.52	
			V_{DDA} = 1.8V		6.78	8.79	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		1.67	3.09	mA
			V_{DDB} = 3.3V		1.65	3.06	
			V_{DDB} = 2.5V		1.64	3.05	
			V_{DDB} = 1.8V		1.59	2.89	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		8.57	10.81	
			V_{DDB} = 3.3V		5.97	7.91	
			V_{DDB} = 2.5V		4.89	6.62	
			V_{DDB} = 1.8V		3.97	5.44	
LOGIC INTERFACE (IN_, OUT_)							
Input High Voltage	V_{IH}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V			0.7 x $V_{DD\_}$		V

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 1*, *Note 3*))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Low Voltage	V_{IL}	1.71V ≤ $V_{DD\_}$ < 2.25V	0.75 x $V_{DD\_}$			V
		2.25V ≤ $V_{DD\_}$ ≤ 5.5V			0.8	
		1.71V ≤ $V_{DD\_}$ < 2.25V			0.7	
Input Hysteresis	V_{HYS}	MAX2266_B/E		410		mV
		MAX2266_C/F		80		
Input Pullup Current	I_{PU}	MAX2266_B/C	-10	-5	-1.5	µA
Input Pulldown Current	I_{PD}	MAX2266_E/F	1.5	5	10	µA
Input Capacitance	C_{IN}	f_{SW} = 1MHz		2		pF
Output Voltage High	V_{OH}	I_{OUT} = -4mA source	$V_{DD\_}$ - 0.4			V
Output Voltage Low	V_{OL}	I_{OUT} = 4mA sink			0.4	V

Dynamic Characteristics - MAX2266_C/MAX2266_F

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 2*, *Note 4*))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	IN_ = GND_ or $V_{DD\_}$ (Note 5)		50		kV/µs
Maximum Data Rate	DR_{MAX}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V	200			Mbps
		1.71V ≤ $V_{DD\_}$ < 2.25V	150			
Minimum Pulse Width	PW_{MIN}	IN_ to OUT_	2.25V ≤ $V_{DD\_}$ ≤ 5.5V			5	ns
			1.71V ≤ $V_{DD\_}$ < 2.25V			6.67	
Propagation Delay (*Figure 1*)	t_{PLH}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	4.4	6.2	9.5	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	4.8	7.0	11.2	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	5.3	8.3	14.7	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	7.1	12.3	22.1	
	t_{PHL}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	4.6	6.5	9.9	
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	5.0	7.3	11.6	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	5.4	8.5	14.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	7.2	12.1	21.8	
Pulse Width Distortion	PWD	|t_{PLH} - t_{PHL}|	4.5V ≤ $V_{DD\_}$ ≤ 5.5V		0.4	2.0	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V		0.4	2.0	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V		0.3	2.0	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V		0	2.0	
	t_{SPLH}		4.5V ≤ $V_{DD\_}$ ≤ 5.5V			3.7	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			4.7	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 2*, *Note 4*))

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Propagation Delay Skew Part-to-Part (Same Channel)		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				6.9	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				12.1	
	t_{SPHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				4.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				4.9	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				7.0	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				11.8	
Propagation Delay Skew Channel-to-Channel (Same Direction) (*Figure 1*)	t_{SCSLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2.0	ns
Propagation Delay Skew Channel-to-Channel (Same Direction (*Figure 1*)	t_{SCSHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2.0	ns
Propagation Delay Skew Channel-to-Channel (Opposite Direction)	t_{SCOLH}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				3.7	ns
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				4.7	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				6.9	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				12.1	
	t_{SCOHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				4.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				4.9	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				7.0	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				11.8	
Peak Eye Diagram Jitter	$t_{JIT(PK)}$	200Mbps			100		ps
Clock Jitter RMS	$t_{JCLK(RMS)}$	500kHz clock input, rising/falling edges			11.1		ps
Rise Time (*Figure 1*)	t_R	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			0.8	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.1	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.5	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			2.4	
Fall Time (*Figure 1*)	t_F	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			1.0	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.4	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			3.0	

Dynamic Characteristics - MAX2266_B/MAX2266_E

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDA} – V_{GNDA} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 2*, *Note 4*))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	IN_ = GND_ or $V_{DD\_}$ (Note 5)		50		kV/µs
Maximum Data Rate	DR_{MAX}		25			Mbps

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDA} - V_{GNDA} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 2*, *Note 4*))

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Minimum Pulse Width	PW_{MIN}	IN_ to OUT_				40	ns
Glitch Rejection		IN_ to OUT_		10	17	29	ns
Propagation Delay (*Figure 1*)	t_{PLH}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	16.7	22.6	30.7	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	17.0	23.4	32.2	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	17.7	24.8	35.3	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	19.6	28.8	42.8	
	t_{PHL}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	16.4	22.7	32.1	
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	16.8	23.5	33.8	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	17.3	24.8	36.7	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	19.0	28.4	43.7	
Pulse Width Distortion	PWD	$|t_{PLH} - t_{PHL}|$	4.5V ≤ $V_{DD\_}$ ≤ 5.5V		0.2	4.0	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V		0.2	4.0	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V		0.3	4.0	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V		0.6	4.0	
Propagation Delay Skew Part-to-Part (Same Channel)	t_{SPLH}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				14.0	ns
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.8	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.2	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.9	
	t_{SPHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				13.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.5	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.4	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.4	
Propagation Delay Skew Channel-to-Channel (Same Direction) (*Figure 1*)	t_{SCSLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4.0	ns
	t_{SCSHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4.0	
Propagation Delay Skew Channel-to-Channel (Opposite Direction)	t_{SCOLH}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				14.0	ns
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.8	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.2	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.9	
	t_{SCOHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				13.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.5	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.4	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.4	
Peak Eye Diagram Jitter	$t_{JIT(PK)}$	25Mbps			250		ps
Rise Time (*Figure 1*)	t_R	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			0.8	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.1	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDA} – V_{GNDA} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (*Note 2*, *Note 4*))

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				1.5	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				2.4	
Fall Time (*Figure 1*)	t_F	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			1.0	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.4	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			3.0	

Note 1: General purpose devices are 100% production tested at T_A = +25°C. Specifications over temperature are guaranteed by design and characterization. Automotive devices are 100% production tested at T_A = +25°C and T_A = +125°C.

Note 2: Not production tested. Guaranteed by design and characterization.

Note 3: All currents into the device are positive. All currents out of the device are negative. All voltages are referenced to their respective grounds (GNDA or GNDB), unless otherwise noted.

Note 4: All measurements are taken with V_{DDA} = V_{DDB}, unless otherwise noted.

Note 5: CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V_{CM} = 1000V).

ESD Protection

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
ESD		Human Body Model, All Pins	±4	kV
ESD		IEC 61000-4-2 Contact, GNDB to GNDA	±8	kV

Test Circuit and Timing Diagram
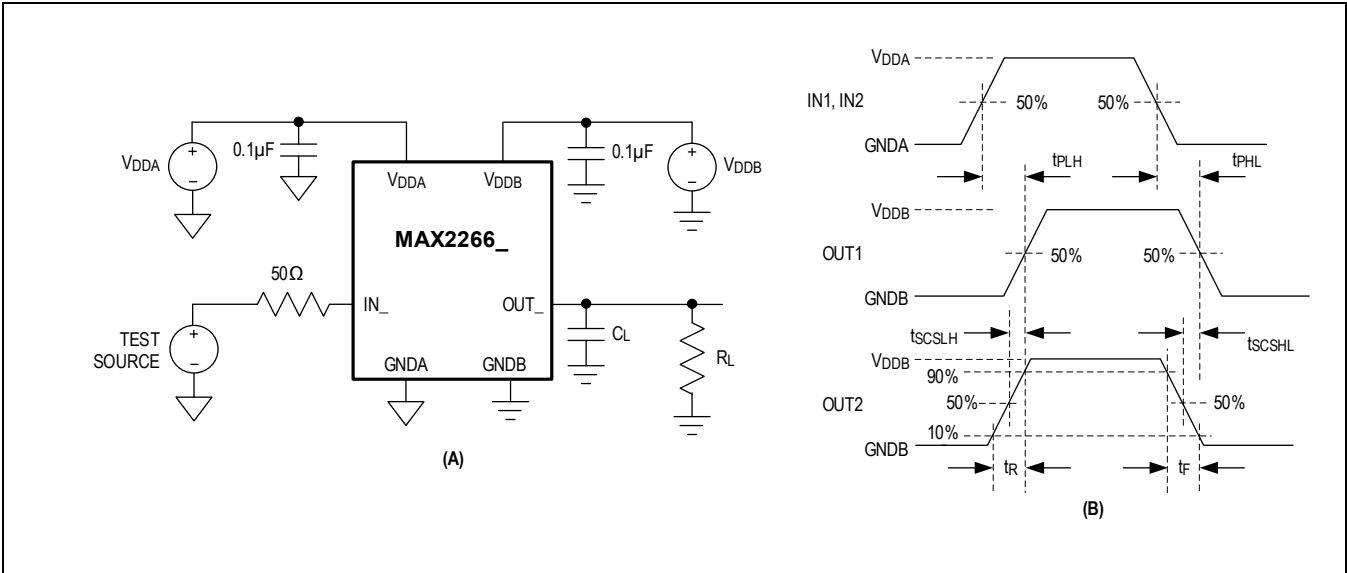
Figure 1. Test Circuit (A) and Timing Diagram (B)

Table 1. Insulation Characteristics

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
Partial Discharge Test Voltage	V_{PR}	Method B1 = V_{IORM} x 1.875 (t = 1s, partial discharge < 5pC)	2250	V_P
Maximum Repetitive Peak Isolation Voltage	V_{IORM}	(Note 6)	1200	V_P
Maximum Working Isolation Voltage	V_{IOWM}	Continuous RMS voltage (Note 6)	848	V_{RMS}
Maximum Transient Isolation Voltage	V_{IOTM}	t = 1s (Note 6)	7000	V_P
Maximum Withstanding Isolation Voltage	V_{ISO}	f_{SW} = 60Hz, duration = 60s (Notes 6, 7)	5000	V_{RMS}
Maximum Surge Isolation Voltage	V_{IOSM}	Reinforced Insulation, test method per IEC 60065, V_{TEST} = 1.6 x V_{IOSM} = 12,800V_{PEAK} (Notes 6, 9)	8000	V_P
Isolation Resistance	R_{IO}	V_{IO} = 500V, T_A = 25°C	>10^{12}	Ω
		V_{IO} = 500V, 100°C ≤ T_A ≤ 125°C	>10^{11}	
		V_{IO} = 500V, T_S = 150°C	>10^9	
Barrier Capacitance Side A to Side B	C_{IO}	f_{SW} = 1MHz (Note 8)	1.5	pF
Minimum Creepage Distance	CPG		8	mm
Minimum Clearance Distance	CLR		8	mm
Internal Clearance		Distance through insulation	0.021	mm
Comparative Tracking Index	CTI	Material Group II (IEC 60112)	>400	
Climate Category			40/125/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	

Note 6: V_{ISO}, V_{IOWM}, V_{IOTM}, V_{IORM}, and V_{IOSM} are defined by the IEC 60747-5-5 standard.

Note 7: The product is qualified at V_{ISO} for 60s and 100% production tested at 120% of V_{ISO} for 1s.

Note 8: Capacitance is measured with all pins on the A side and the B side tied together.

**Note 9:** Devices are immersed in oil during surge characterization.

Safety Regulatory Approvals

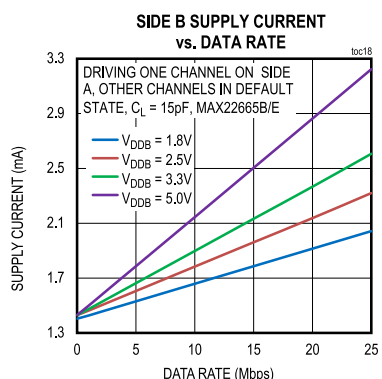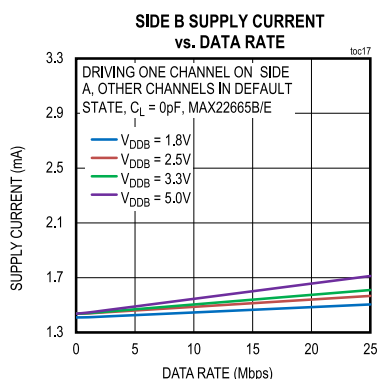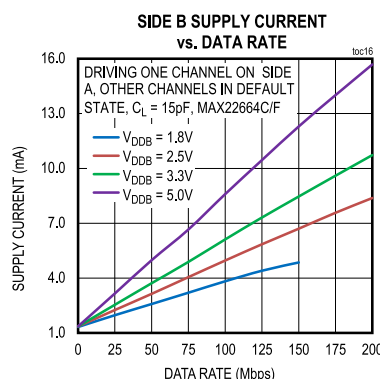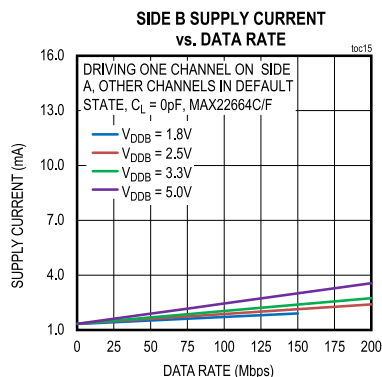| UL |
|---|
| The MAX22663-MAX22666 are certified under UL1577. For more details, refer to File E351759. |
| Rated up to 5000V_{RMS} isolation voltage for single protection. |
| **cUL (Equivalent to CSA notice 5A)** |
| The MAX22663−MAX22666 are certified up to 5000V_{RMS} for single protection. For more details, refer to File E351759. |
| **VDE (Pending)** |
| The MAX22663−MAX22666 are certified to DIN VDE V 0884-11: 2017-1. Reinforced Insulation, Maximum Transient Isolation Voltage 7000V_{PK}, Maximum Repetitive Peak Isolation Voltage 1200V_{PK}. |

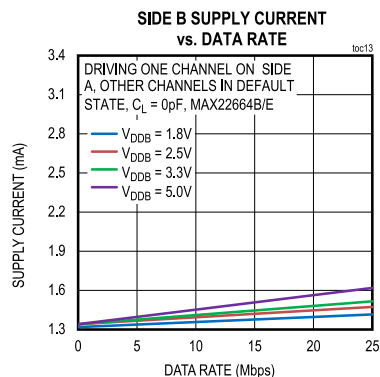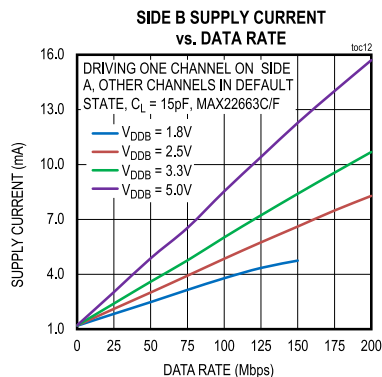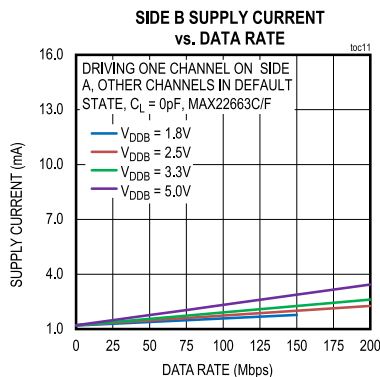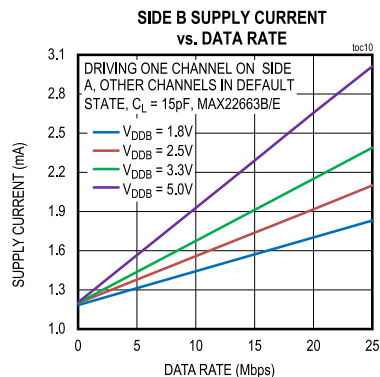*These couplers are suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.*
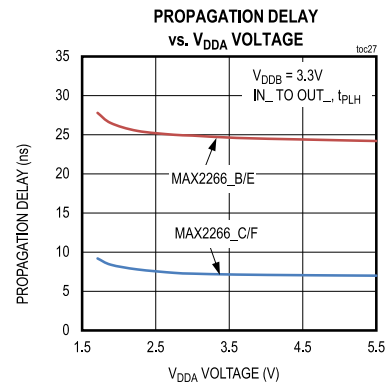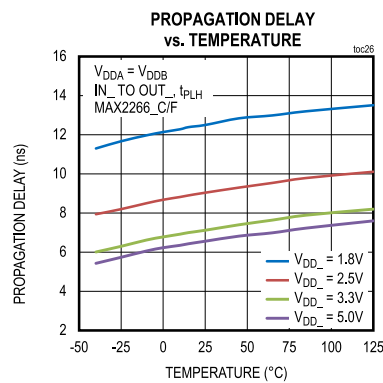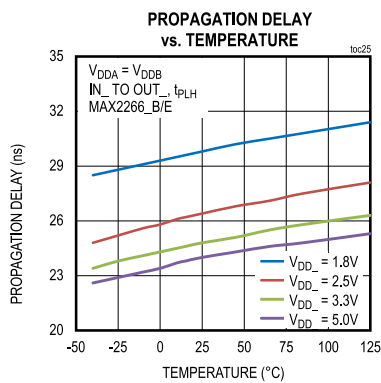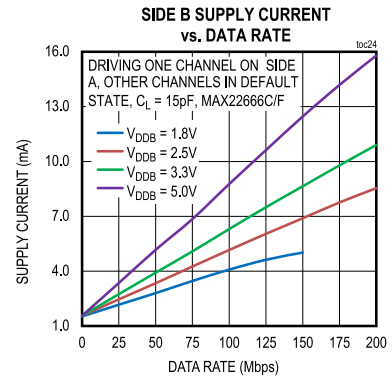
Typical Operating Characteristics
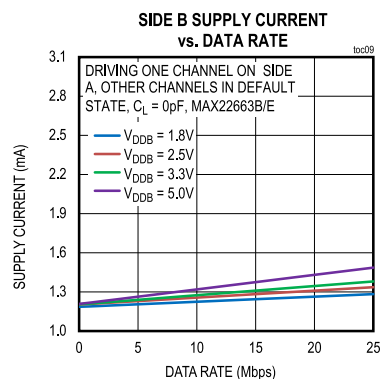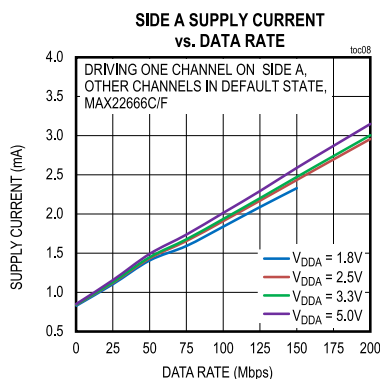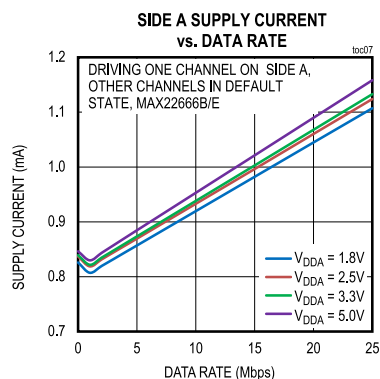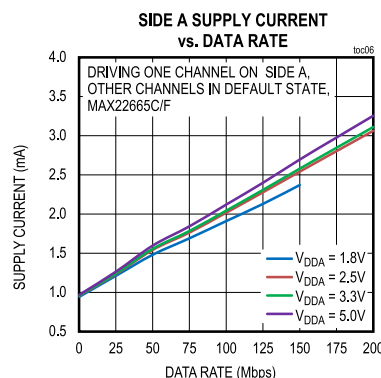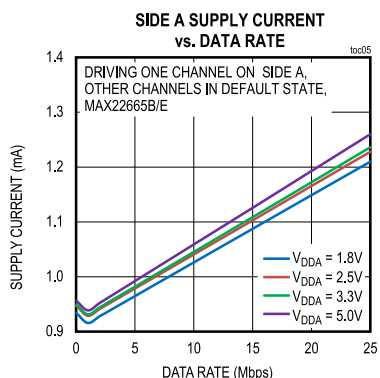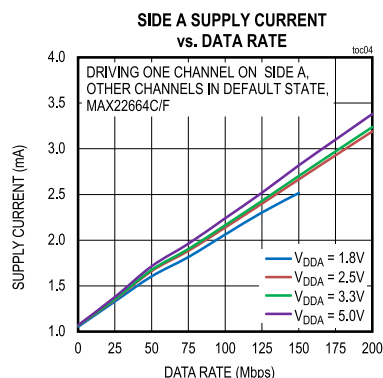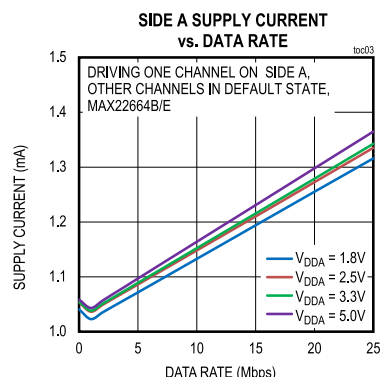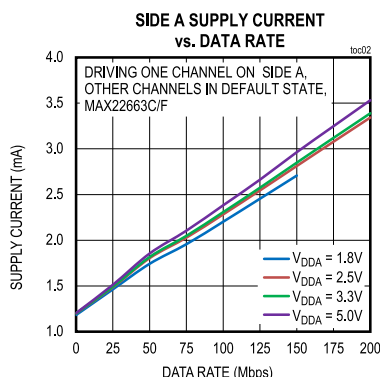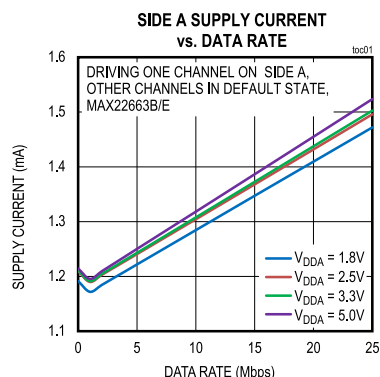
(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

$(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C,$ unless otherwise noted.)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc10)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22663B/E
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc11)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22663C/F
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc12)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22663C/F
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc13)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22664B/E
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc14)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22664B/E
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc15)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22664C/F
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc16)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22664C/F
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc17)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22665B/E
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

SIDE B SUPPLY CURRENT vs. DATA RATE (toc18)

DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22665B/E
- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

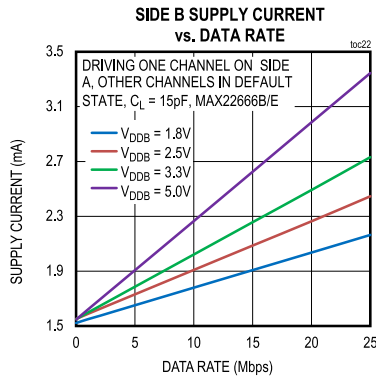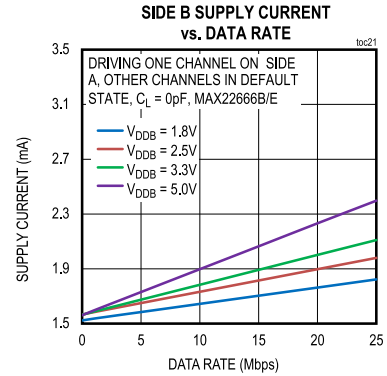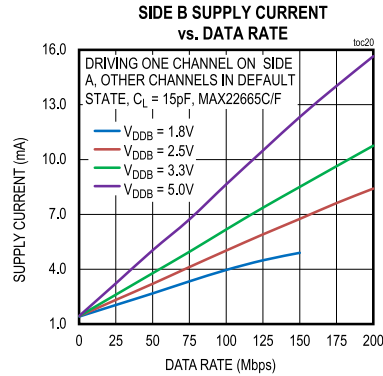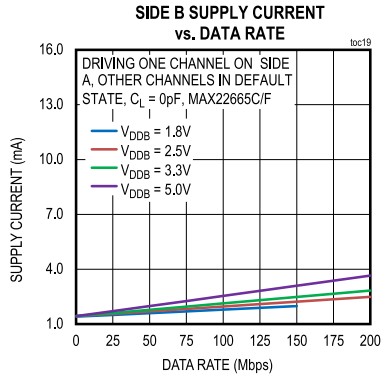SUPPLY CURRENT (mA) vs DATA RATE (Mbps)

(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

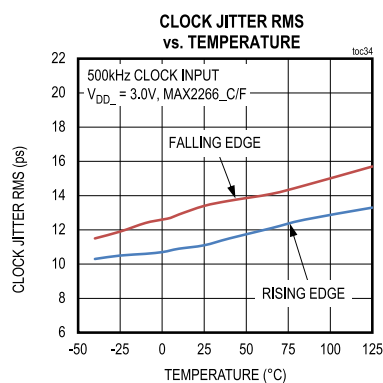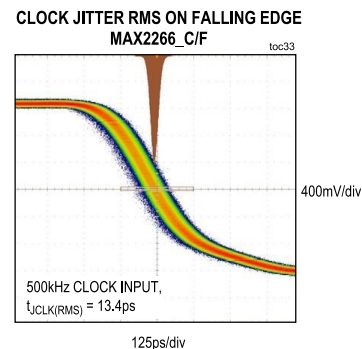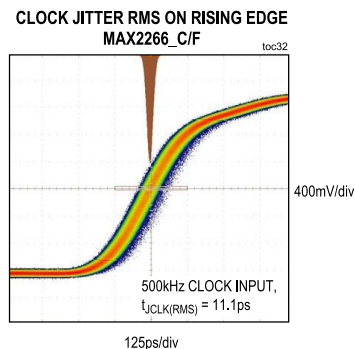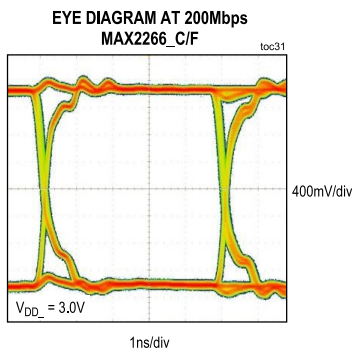SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22665C/F (toc19)

SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22665C/F (toc20)

SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22666B/E (toc21)

SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22666B/E (toc22)

SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 0pF, MAX22666C/F (toc23)

SIDE B SUPPLY CURRENT vs. DATA RATE — DRIVING ONE CHANNEL ON SIDE A, OTHER CHANNELS IN DEFAULT STATE, C_L = 15pF, MAX22666C/F (toc24)

PROPAGATION DELAY vs. TEMPERATURE — V_{DDA} = V_{DDB}, IN_ TO OUT_, t_{PLH}, MAX2266_B/E (toc25)

PROPAGATION DELAY vs. TEMPERATURE — V_{DDA} = V_{DDB}, IN_ TO OUT_, t_{PLH}, MAX2266_C/F (toc26)

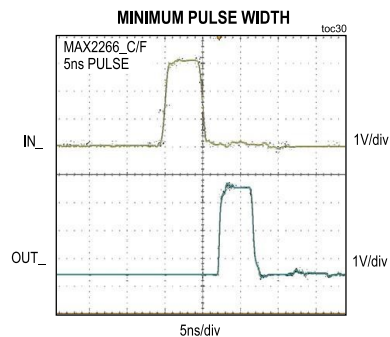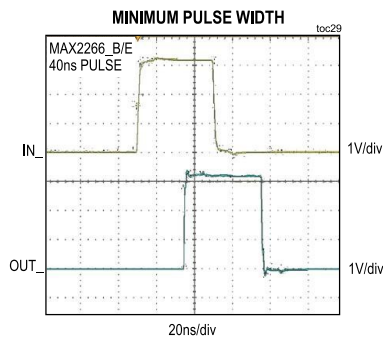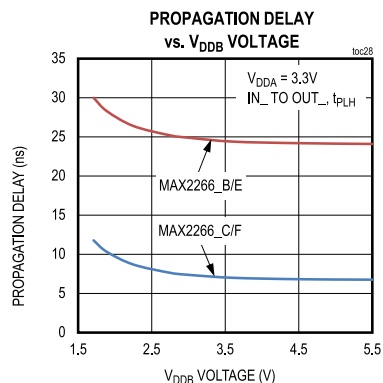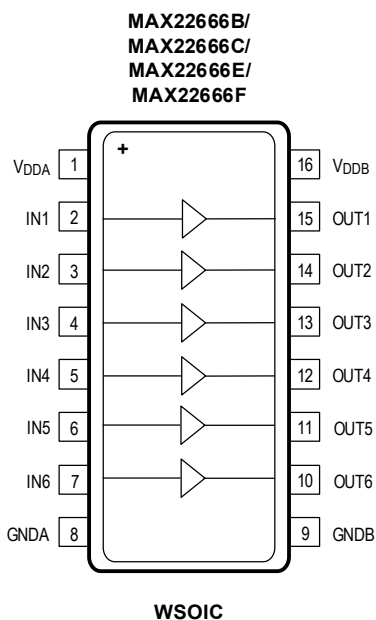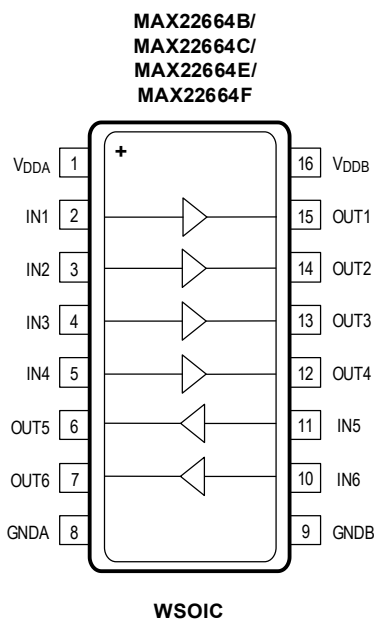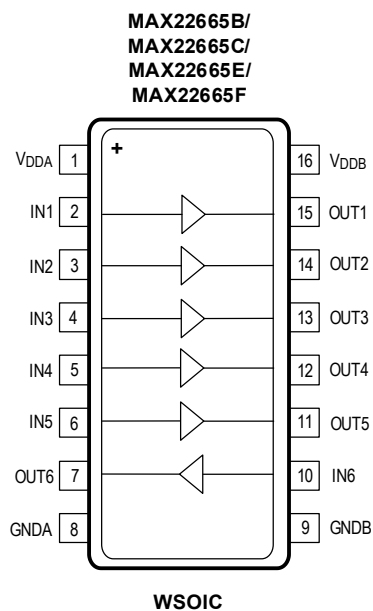PROPAGATION DELAY vs. V_{DDA} VOLTAGE — V_{DDB} = 3.3V, IN_ TO OUT_, t_{PLH} (toc27)

(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)
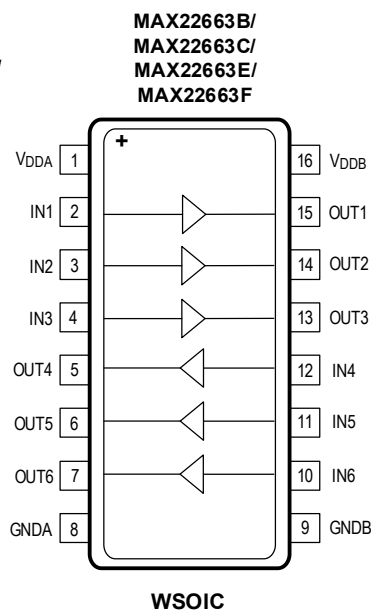
PROPAGATION DELAY vs. V_{DDB} VOLTAGE

toc28

V_{DDA} = 3.3V
IN_ TO OUT_, t_{PLH}

MAX2266_B/E

MAX2266_C/F

MINIMUM PULSE WIDTH

toc29

MAX2266_B/E
40ns PULSE

IN_   1V/div

OUT_   1V/div

20ns/div

MINIMUM PULSE WIDTH

toc30

MAX2266_C/F
5ns PULSE

IN_   1V/div

OUT_   1V/div

5ns/div

EYE DIAGRAM AT 200Mbps MAX2266_C/F

toc31

400mV/div

$V_{DD_}$ = 3.0V

1ns/div

CLOCK JITTER RMS ON RISING EDGE MAX2266_C/F

toc32

400mV/div

500kHz CLOCK INPUT,
$t_{JCLK(RMS)}$ = 11.1ps

125ps/div

CLOCK JITTER RMS ON FALLING EDGE MAX2266_C/F

toc33

400mV/div

500kHz CLOCK INPUT,
$t_{JCLK(RMS)}$ = 13.4ps

125ps/div

CLOCK JITTER RMS vs. TEMPERATURE

toc34

500kHz CLOCK INPUT
$V_{DD_}$ = 3.0V, MAX2266_C/F

FALLING EDGE

RISING EDGE

Pin Configurations

TOP VIEW

**MAX22663B/
MAX22663C/
MAX22663E/
MAX22663F**

V$_{DDA}$ 1		16 V$_{DDB}$
IN1 2		15 OUT1
IN2 3		14 OUT2
IN3 4		13 OUT3
OUT4 5		12 IN4
OUT5 6		11 IN5
OUT6 7		10 IN6
GNDA 8		9 GNDB

WSOIC

**MAX22665B/
MAX22665C/
MAX22665E/
MAX22665F**

V$_{DDA}$ 1		16 V$_{DDB}$
IN1 2		15 OUT1
IN2 3		14 OUT2
IN3 4		13 OUT3
IN4 5		12 OUT4
IN5 6		11 OUT5
OUT6 7		10 IN6
GNDA 8		9 GNDB

WSOIC

**MAX22664B/
MAX22664C/
MAX22664E/
MAX22664F**

V$_{DDA}$ 1		16 V$_{DDB}$
IN1 2		15 OUT1
IN2 3		14 OUT2
IN3 4		13 OUT3
IN4 5		12 OUT4
OUT5 6		11 IN5
OUT6 7		10 IN6
GNDA 8		9 GNDB

WSOIC

**MAX22666B/
MAX22666C/
MAX22666E/
MAX22666F**

V$_{DDA}$ 1		16 V$_{DDB}$
IN1 2		15 OUT1
IN2 3		14 OUT2
IN3 4		13 OUT3
IN4 5		12 OUT4
IN5 6		11 OUT5
IN6 7		10 OUT6
GNDA 8		9 GNDB

WSOIC

Pin Descriptions

PIN				NAME	FUNCTION
MAX22663	MAX22664	MAX22665	MAX22666		
1	1	1	1	V_{DDA}	Power Supply Input for Side A. Bypass V_{DDA} to GNDA with a 0.1µF ceramic capacitor as close as possible to the pin.
2	2	2	2	IN1	Logic Input 1 on Side A. Corresponds to Logic Output 1 on Side B.
3	3	3	3	IN2	Logic Input 2 on Side A. Corresponds to Logic Output 2 on Side B.
4	4	4	4	IN3	Logic Input 3 on Side A. Corresponds to Logic Output 3 on Side B.
12	5	5	5	IN4	Logic Input 4 on Side A/B. Corresponds to Logic Output 4 on Side B/A.
11	11	6	6	IN5	Logic Input 5 on Side A/B. Corresponds to Logic Output 5 on Side B/A.
10	10	10	7	IN6	Logic Input 6 on Side A/B. Corresponds to Logic Output 6 on Side B/A.
8	8	8	8	GNDA	Ground Reference for Side A.
9	9	9	9	GNDB	Ground Reference for Side B.
7	7	7	10	OUT6	Logic Output 6 on Side B/A. OUT6 is the logic output for the IN6 input on Side A/B.
6	6	11	11	OUT5	Logic Output 5 on Side B/A. OUT5 is the logic output for the IN5 input on Side A/B.
5	12	12	12	OUT4	Logic Output 4 on Side B/A. OUT4 is the logic output for the IN4 input on Side A/B.
13	13	13	13	OUT3	Logic Output 3 on Side B. OUT3 is the logic output for the IN3 input on Side A.
14	14	14	14	OUT2	Logic Output 2 on Side B. OUT2 is the logic output for the IN2 input on Side A.
15	15	15	15	OUT1	Logic Output 1 on Side B. OUT1 is the logic output for the IN1 input on Side A.
16	16	16	16	V_{DDB}	Power Supply Input for Side B. Bypass V_{DDB} to GNDB with a 0.1µF ceramic capacitor as close as possible to the pin.

Functional Diagrams
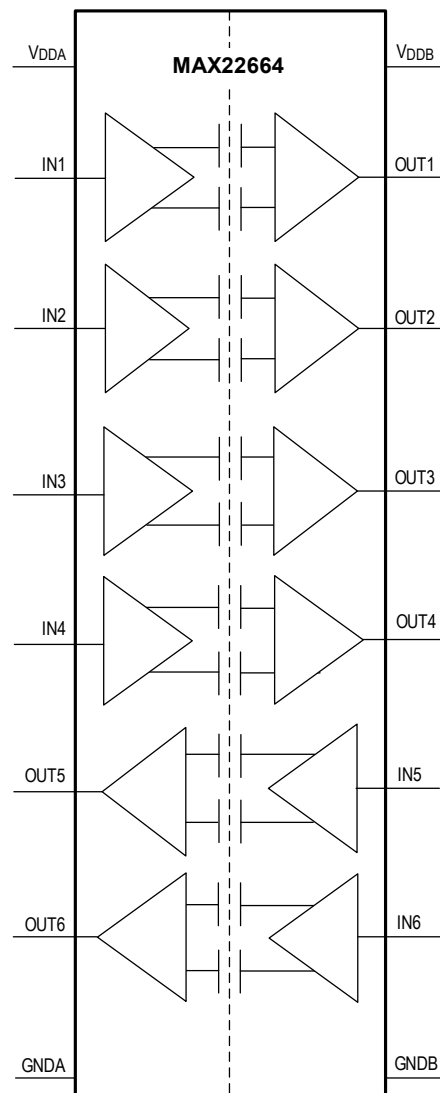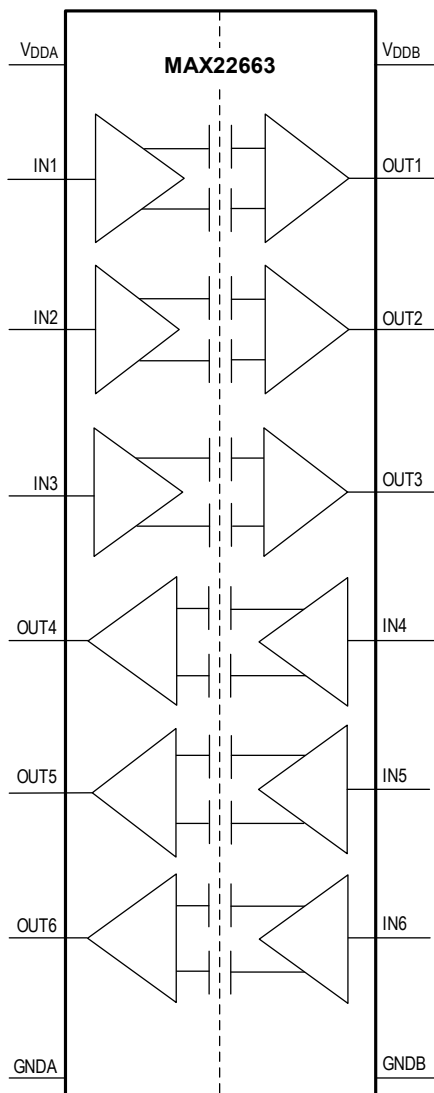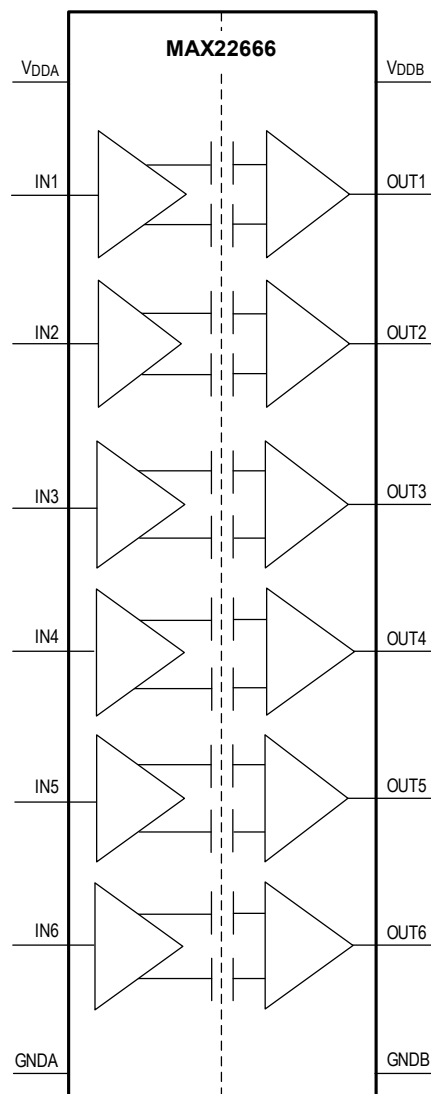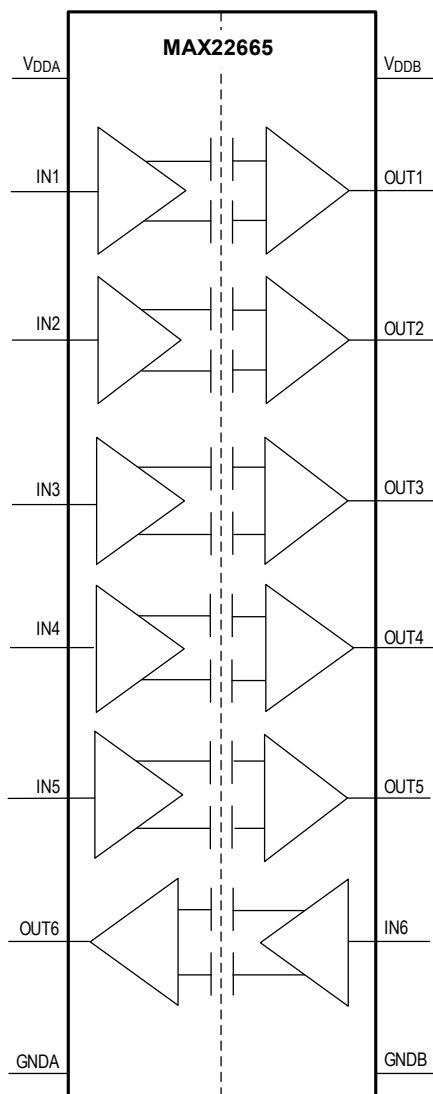
Detailed Description

The MAX22663−MAX22666 are a family of 6-channel reinforced digital isolators in a 16 Wide SOIC package, with an isolation rating of 5kV$_{RMS}$. This family of devices offers all possible unidirectional channel configurations to accommodate any 6-channel design.

The MAX22663 features three channels transmitting digital signals in one direction and three channels transmitting in the opposite direction for applications such as isolated micro-controller interface. The MAX22664 offers four channels transmitting digital signals in one direction and two channels transmitting in the opposite direction, making them ideal candidates for applications such as isolated SPI. The MAX22665 provides five channels transmitting digital signals in one direction and one channel transmitting in the opposite direction. The MAX22666 features all six channels transmitting digital signals in one direction, which is suitable for applications such as isolated digital I/O.

The MAX22663-MAX22666 are available in a 16 Wide SOIC package with 8mm creepage and clearance, with an isolation rating of 5kV$_{RMS}$. This family of digital isolators offers the low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Analog Devices' proprietary process technology. The devices isolate different ground domains and block high-voltage/high-current transients from sensitive or human interface circuitry.

Devices are available with a maximum data rate of either 25Mbps (B/E version) or 200Mbps (C/F version). The MAX2266_B/C feature default-high outputs. The MAX2266_E/F feature default-low outputs. The default is the state the output assumes when the input is not powered or if the input is open-circuit. The MAX22663-MAX22666 has two supply inputs (V$_{DDA}$ and V$_{DDB}$) that independently set the logic levels on either side of the device. V$_{DDA}$ and V$_{DDB}$ are referenced to GNDA and GNDB, respectively. The MAX22663-MAX22666 also features a refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

Digital Isolation

The family of devices provides reinforced galvanic isolation for digital signals that are transmitted between two ground domains. The MAX22663-MAX22666 can withstand differences of up to 5kV$_{RMS}$ for up to 60 seconds, and up to 1200V$_{PEAK}$ of continuous isolation.

AEC-Q100 Qualification

Devices with /V suffix are AEC-Q100 qualified. See the *Ordering Information* for all automotive grade part numbers.

Level Shifting

The wide supply voltage range of both V$_{DDA}$ and V$_{DDB}$ allows the MAX22663-MAX22666 to be used for level translation in addition to isolation. V$_{DDA}$ and V$_{DDB}$ can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

Unidirectional Channels

Each channel of the device is unidirectional; it only passes data in one direction, as shown in the *Functional Diagrams*. All devices feature six unidirectional channels that operate independently with guaranteed data rates from DC to 25Mbps (B/E version), or from DC to 200Mbps (C/F version). The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs are able to drive both TTL and CMOS logic inputs.

Startup and Undervoltage-Lockout

The V$_{DDA}$ and V$_{DDB}$ supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply, all outputs go to their default states regardless of the state of the inputs as seen in *Table 2 Figure 2* through *Figure 5* show the behavior of the outputs during power-up and power-down.

Table 2. Output Behavior During Undervoltage Conditions

V$_{IN\_}$	V$_{DDA}$	V$_{DDB}$	V$_{OUTA}$	V$_{OUTB}$
1	Powered	Powered	High	High
0	Powered	Powered	Low	Low
X	Undervoltage	Powered	Default	Default
X	Powered	Undervoltage	Default	Default

Note: "X" is don't care.
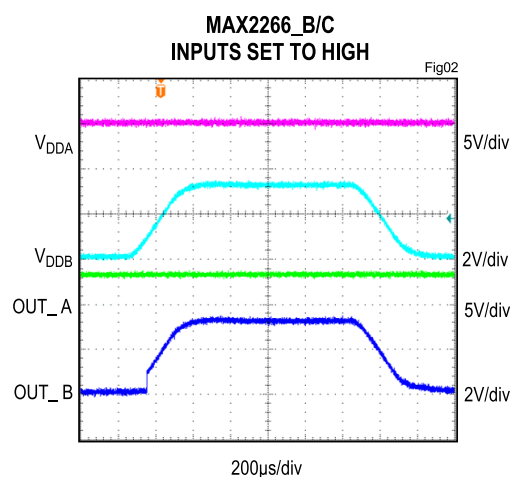
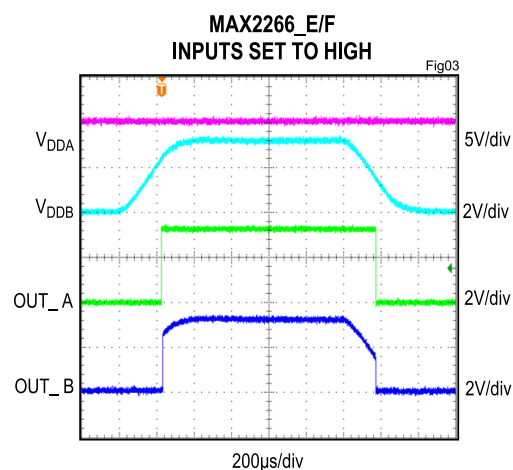Figure 2. Undervoltage Lockout Behavior, MAX2266_B/C, Inputs set to High

Figure 3. Undervoltage Lockout Behavior, MAX2266_E/F, Inputs set to High
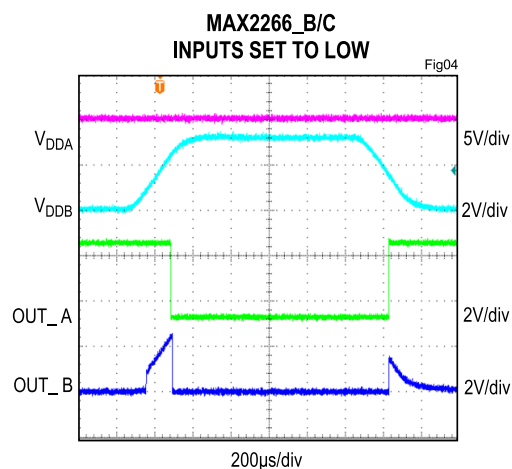

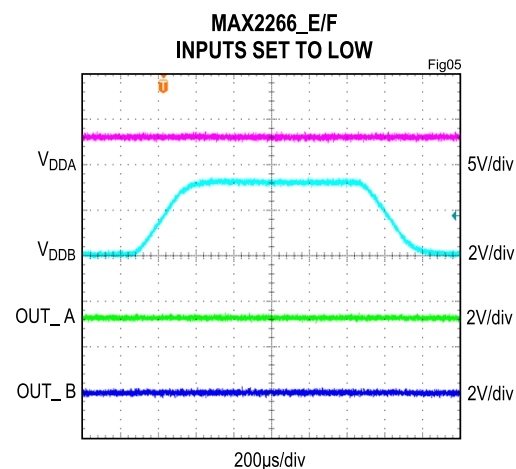Figure 4. Undervoltage Lockout Behavior, MAX2266_B/C, Inputs set to Low

Figure 5. Undervoltage Lockout Behavior, MAX2266_E/F, Inputs set to Low

Safety Limit

Damage to the IC can result in a low-resistance path to ground or to the supply and, without current limiting, the MAX22663-MAX22666 can dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. _Table 3_ shows the safety limits for the MAX22663–MAX22666.

The maximum safety temperature (T_S) for the device is the 150°C maximum junction temperature specified in the _Absolute Maximum Ratings_. The power dissipation (P_D) and junction-to-ambient thermal impedance (θ_{JA}) determine the junction temperature. Thermal impedance values (θ_{JA} and θ_{JC}) are available in the _Package Information_ section and power dissipation calculations are discussed in the _Calculating Power Dissipation_ section. Calculate the junction temperature (T_J) as:

$$T_J = T_A + (P_D \times \theta_{JA})$$

Figure 6 shows the thermal derating curve for safety limiting the power of the devices, and _Figure 7_ shows the thermal derating curve for safety limiting the current of the devices. Ensure that the junction temperature does not exceed 150°C.
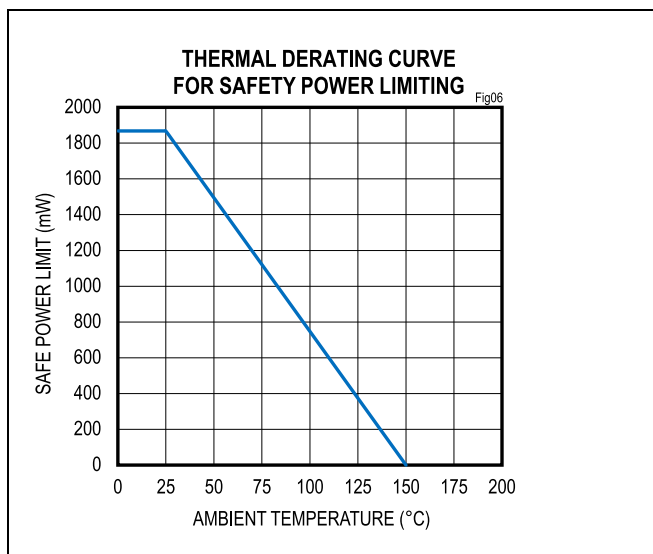

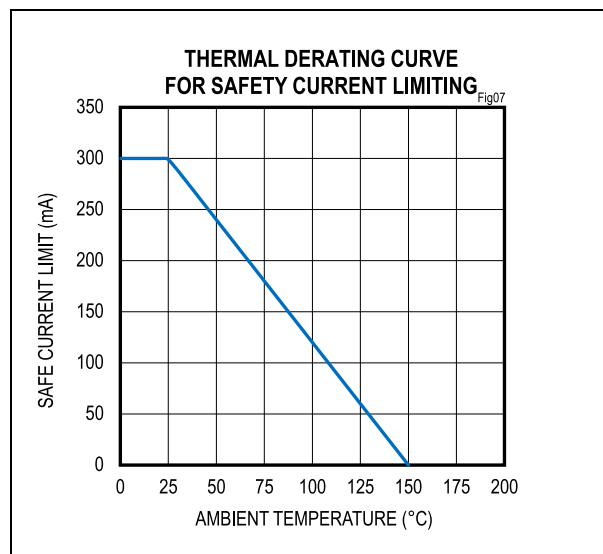Figure 6. Thermal Derating Curve for Safety Power Limiting

Figure 7. Thermal Derating Curve for Safety Current Limiting

Table 3. Safety Limiting Values

PARAMETER	SYMBOL	TEST CONDITIONS	MAX	UNIT
Safety Current on Any Pin (No Damage to Isolation Barrier)	I_S	$T_J = 150°C$, $T_A = 25°C$	300	mA
Total Safety Power Dissipation	P_S	$T_J = 150°C$, $T_A = 25°C$	1868	mW
Maximum Safety Temperature	T_S		150	°C

Applications Information

Power-Supply Sequencing

The MAX22663-MAX22666 do not require any special power supply sequencing. The logic levels are set independently on either side by V_{DDA} and V_{DDB}. Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

Power-Supply Decoupling

To reduce ripple and the chance of introducing data errors, bypass V_{DDA} and V_{DDB} with 0.1µF low-ESR ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power supply input pins as possible.

Layout Considerations

The PCB designer should follow some critical recommendations in order to get the best performance from the design.

- Keep the input/output traces as short as possible. To keep signal paths low-inductance, avoid using vias.
- Have a solid ground plane underneath the high-speed signal layer.
- Keep the area underneath the devices free from ground and signal planes. Any galvanic or metallic connection between Side A and Side B defeats the isolation.

Calculating Power Dissipation

The required current for a given supply (V_{DDA} or V_{DDB}) can be estimated by summing the current required for each channel. The supply current for a channel depends on whether the channel is an input or an output, the channel's data rate, and the capacitive or resistive load if it is an output. The typical current for input or output at any data rate can be estimated from the graphs in *Figure 8* and *Figure 9*. Note that the data in *Figure 8* and *Figure 9* are extrapolated from the supply current measurements in a typical operating condition.

The total current for a single channel is the sum of the no-load current (shown in *Figure 8* and *Figure 9*) which is a function of voltage and data rate, and the load current, which depends on the type of load. Current into a capacitive load is a function of the load capacitance, the switching frequency, and the supply voltage.

$$I_{CL} = C_L \times f_{SW} \times V_{DD}$$

where:

I_{CL} is the current required to drive the capacitive load.

C_L is the load capacitance on the isolator's output pin.

f_{SW} is the switching frequency (bits per second/2).

V_{DD} is the supply voltage on the output side of the isolator.

Current into a resistive load depends on the load resistance, the supply voltage, and the average duty cycle of the data waveform. The DC load current can be conservatively estimated by assuming the output is always high.

$$I_{RL} = V_{DD} \div R_L$$

where:

I_{RL} is the current required to drive the resistive load.

V_{DD} is the supply voltage on the output side of the isolator.

R_L is the load resistance on the isolator's output pin.

Example (See *Figure 10*): A MAX22664C is operating with V_{DDA} = 2.5V, V_{DDB} = 3.3V, channel 1 operating at 20Mbps with a 15kΩ resistive load; channel 2 operating at 100Mbps with a 10pF capacitive load; channel 3 is not in use and the resistive load is negligible since the isolator is driving a CMOS input; channel 4 held high with a 10kΩ resistive load; channel 5 operating at 50Mbps with a 20kΩ resistive load; and channel 6 operating at 200Mbps with a 15pF capacitive load. Refer to *Table 4* and *Table 5* for V_{DDA} and V_{DDB} supply current calculation worksheets.

V$_{DDA}$ must supply (with V$_{DDA}$ = 2.5V):

- Channel 1 is an input channel operating at 2.5V and 20Mbps, consuming 0.35mA, estimated from *Figure 8*.
- Channel 2 is an input channel operating at 2.5V and 100Mbps, consuming 1.19mA, estimated from *Figure 8*.
- Channels 3 and 4 are input channels operating at 2.5V with DC signal, consuming 0.14mA, estimated from *Figure 8*.
- Channel 5 is an output channel operating at 2.5V and 50Mbps, consuming 0.52mA, estimated from *Figure 9*.
- I$_{RL}$ on channel 5 for 20kΩ resistive load at 2.5V and switching at 50Mbps with 50% duty cycle is 0.0625mA.
- Channel 6 is an output channel operating at 2.5V and 200Mbps, consuming 1.31mA, estimated from *Figure 9*.
- I$_{CL}$ on channel 6 for 15pF capacitive load at 2.5V and 200Mbps is 3.75mA.

Total current for Side A = 7.46mA (typ).

V$_{DDB}$ must supply (with V$_{DDB}$ = 3.3V):

- Channel 1 is an output channel operating at 3.3V and 20Mbps, consuming 0.40mA, estimated from *Figure 9*.
- I$_{RL}$ on channel 1 for 15kΩ resistive load at 3.3V and switching at 20Mbps with 50% duty cycle is 0.11mA.
- Channel 2 is an output channel operating at 3.3V and 100Mbps, consuming 0.96mA, estimated from *Figure 9*.
- I$_{CL}$ on channel 2 for 10pF capacitive load at 3.3V and 100Mbps is 1.65mA.
- Channels 3 and 4 are output channels operating at 3.3V with DC signal, consuming 0.26mA, estimated from *Figure 9*.
- I$_{RL}$ on channel 4 for 10kΩ resistive load held at 3.3V is 0.33mA.
- Channel 5 is an input channel operating at 3.3V and 50Mbps, consuming 0.68mA, estimated from *Figure 8*.
- Channel 6 is an input channel operating at 3.3V and 200Mbps, consuming 2.29mA, estimated from *Figure 8*.

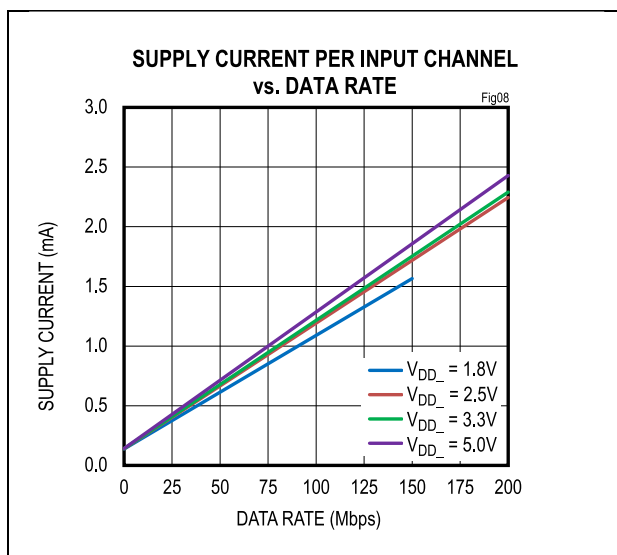Total current for Side B = 6.94mA (typ).

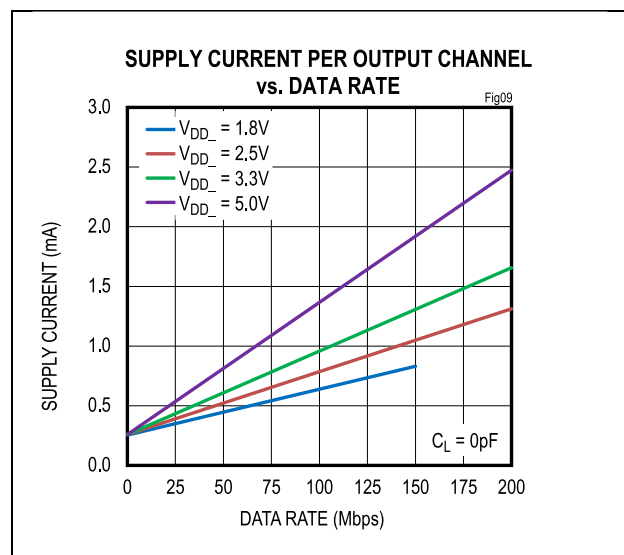Figure 8. Supply Current Per Input Channel (Calculated)

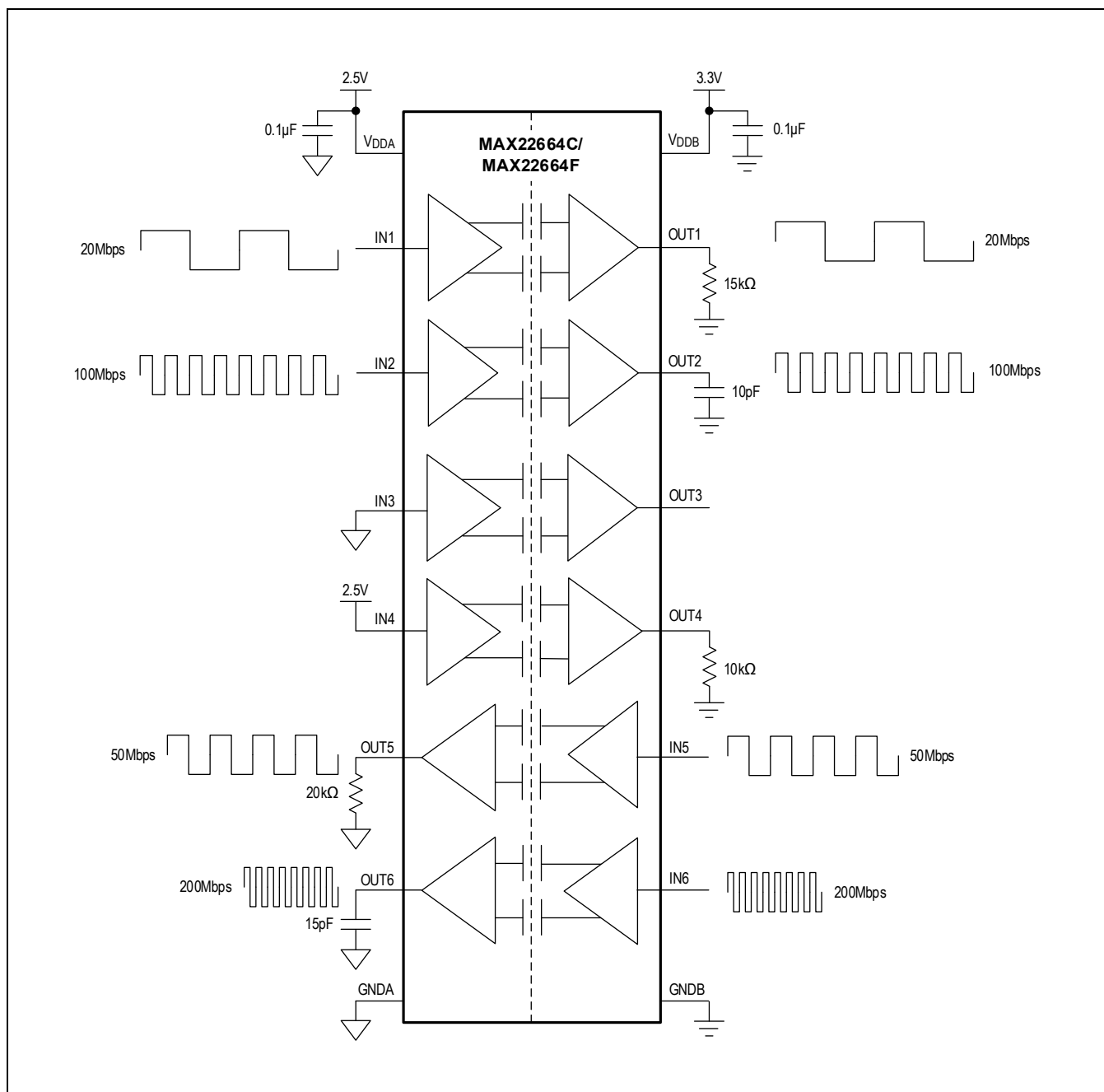Figure 9. Supply Current Per Output Channel (Calculated)

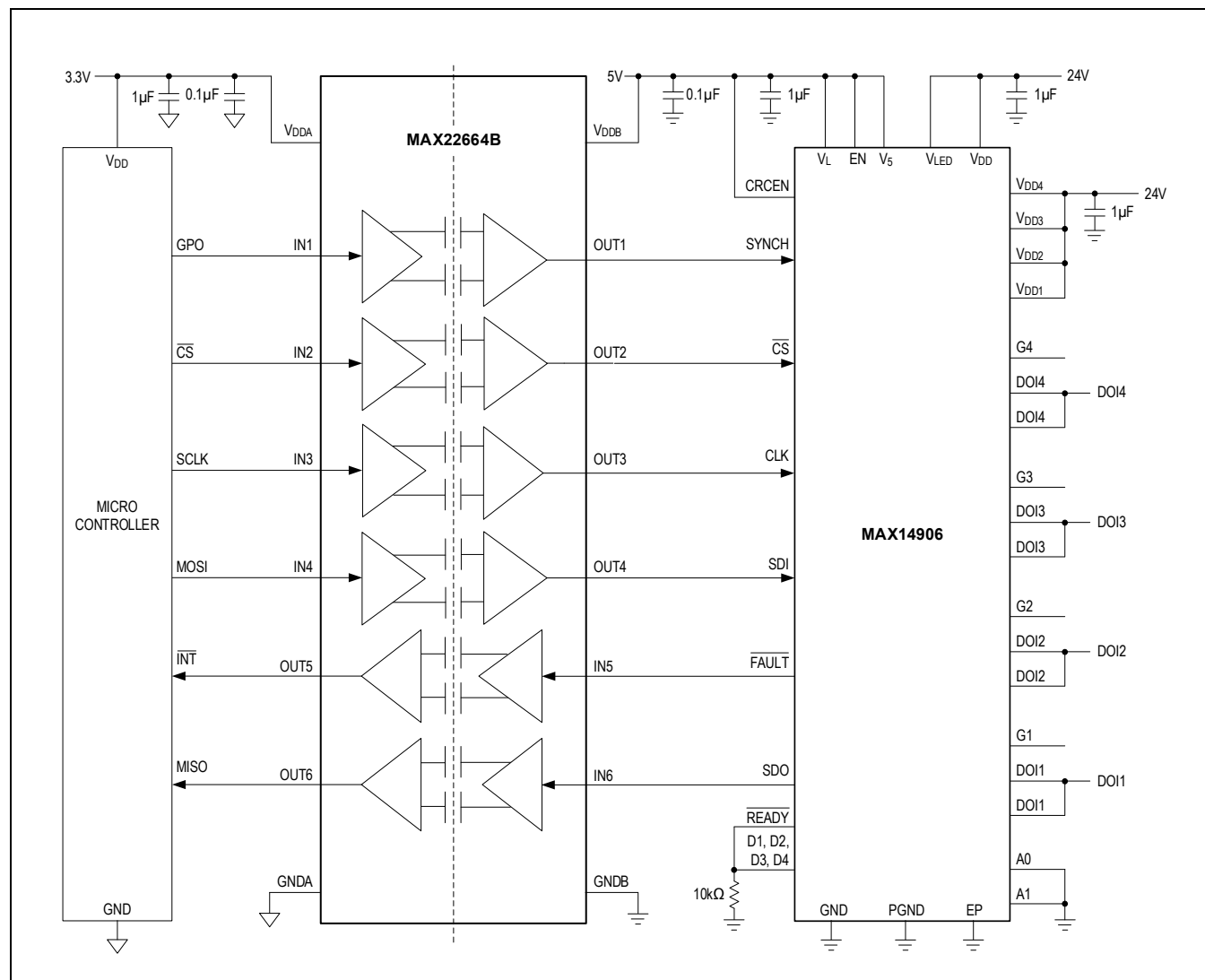Figure 10. Example Circuit for Supply Current Calculation

Table 4. Side A Supply Current Calculation Worksheet

SIDE A					V_{DDA} = 2.5V	
CHANNEL	IN/OUT	DATA RATE (Mbps)	LOAD TYPE	LOAD	"NO LOAD" CURRENT (mA)	LOAD CURRENT (mA)
1	IN	20			0.35	
2	IN	100			1.19	
3	IN	0			0.14	
4	IN	0			0.14	
5	OUT	50	Resistive	20kΩ	0.52	2.5V / 20kΩ x 0.5 = 0.0625mA
6	OUT	200	Capacitive	15pF	1.31	2.5V x 100MHz x 15pF = 3.75mA
Total: 7.46mA						

Table 5. Side B Supply Current Calculation Worksheet

SIDE B					V_{DDB} = 3.3V	
CHANNEL	IN/OUT	DATA RATE (Mbps)	LOAD TYPE	LOAD	"NO LOAD" CURRENT (mA)	LOAD CURRENT (mA)
1	OUT	20	Resistive	15kΩ	0.40	3.3V / 15kΩ x 0.5 = 0.11mA
2	OUT	100	Capacitive	10pF	0.96	3.3V x 50MHz x 10pF = 1.65mA
3	OUT	0			0.26	
4	OUT	0	Resistive	10kΩ	0.26	3.3V / 10kΩ = 0.33mA
5	IN	50			0.68	
6	IN	200			2.29	
Total: 6.94mA						

Typical Application Circuit

Reinforced, Fast, Low-Power, Six-Channel Digital Isolators

Product Selector Guide

MAX2266 4 C A W E /V +

CHANNEL
CONFIGURATION
6: 6/0
5: 5/1
4: 4/2
3: 3/3

LEAD-FREE/ROHS COMPLIANT

/V: AUTOMOTIVE GRADE PART
BLANK: GENERAL PURPOSE PART

PINS
E: 16

DEVICE CONFIGURATION	MAXIMUM DATA RATE	
	25Mbps	200Mbps
DEFAULT-HIGH OUTPUT	B	C
DEFAULT-LOW OUTPUT	E	F

PACKAGE TYPE
W: WIDE SOIC

TEMP RANGE
-40°C TO +125°C
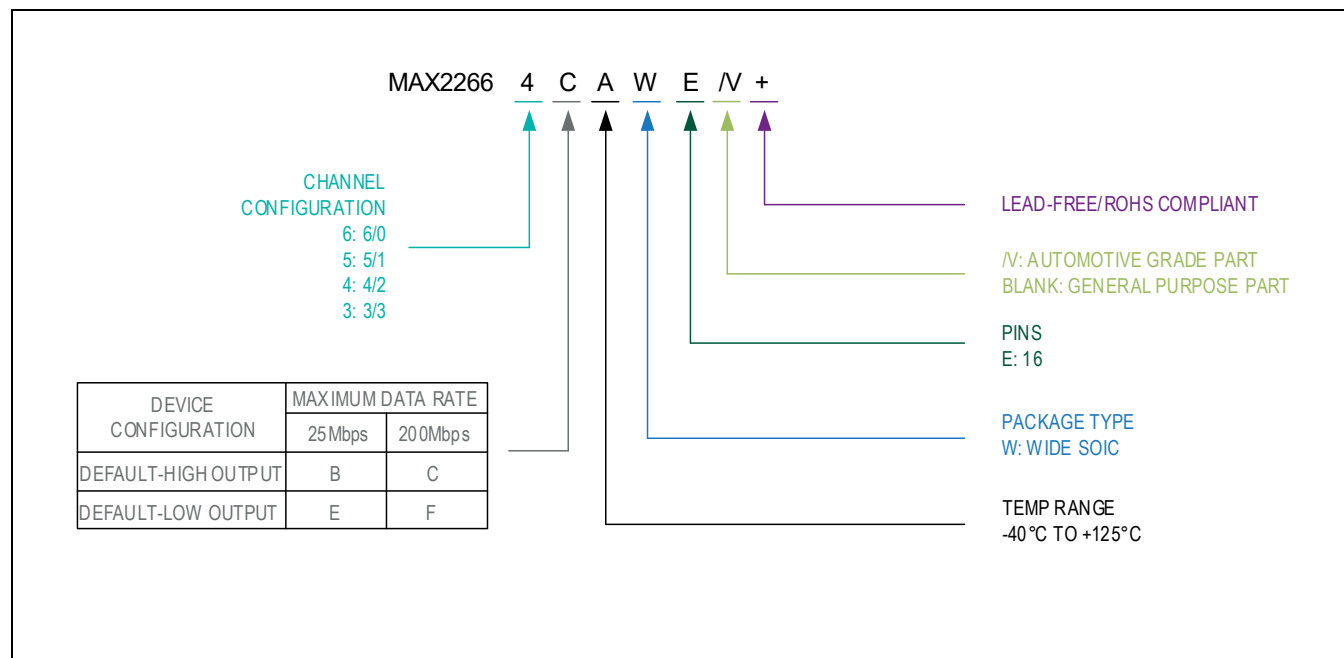
Ordering Information

PART NUMBER	CHANNEL CONFIGURATION	DATA RATE (Mbps)	DEFAULT OUTPUT	ISOLATION VOLTAGE (kV$_{RMS}$)	TEMPERATURE RANGE	PIN-PACKAGE
GENERAL PURPOSE DEVICES						
MAX22663BAWE+*	3/3	25	High	5	-40°C to +125°C	16-WSOIC
MAX22663CAWE+*	3/3	200	High	5	-40°C to +125°C	16-WSOIC
MAX22663EAWE+*	3/3	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22663FAWE+*	3/3	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22664BAWE+*	4/2	25	High	5	-40°C to +125°C	16-WSOIC
MAX22664CAWE+	4/2	200	High	5	-40°C to +125°C	16-WSOIC
MAX22664EAWE+*	4/2	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22664FAWE+*	4/2	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22665BAWE+*	5/1	25	High	5	-40°C to +125°C	16-WSOIC
MAX22665CAWE+*	5/1	200	High	5	-40°C to +125°C	16-WSOIC
MAX22665EAWE+*	5/1	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22665FAWE+	5/1	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22666BAWE+*	6/0	25	High	5	-40°C to +125°C	16-WSOIC
MAX22666CAWE+	6/0	200	High	5	-40°C to +125°C	16-WSOIC
MAX22666EAWE+*	6/0	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22666FAWE+*	6/0	200	Low	5	-40°C to +125°C	16-WSOIC
AUTOMOTIVE DEVICES						

MAX22663BAWE/V+*	3/3	25	High	5	-40°C to +125°C	16-WSOIC
MAX22663CAWE/V+*	3/3	200	High	5	-40°C to +125°C	16-WSOIC
MAX22663EAWE/V+*	3/3	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22663FAWE/V+*	3/3	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22664BAWE/V+*	4/2	25	High	5	-40°C to +125°C	16-WSOIC
MAX22664CAWE/V+	4/2	200	High	5	-40°C to +125°C	16-WSOIC
MAX22664EAWE/V+*	4/2	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22664FAWE/V+*	4/2	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22665BAWE/V+*	5/1	25	High	5	-40°C to +125°C	16-WSOIC
MAX22665CAWE+/V*	5/1	200	High	5	-40°C to +125°C	16-WSOIC
MAX22665EAWE+/V*	5/1	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22665FAWE+/V*	5/1	200	Low	5	-40°C to +125°C	16-WSOIC
MAX22666BAWE+/V*	6/0	25	High	5	-40°C to +125°C	16-WSOIC
MAX22666CAWE+/V*	6/0	200	High	5	-40°C to +125°C	16-WSOIC
MAX22666EAWE+/V*	6/0	25	Low	5	-40°C to +125°C	16-WSOIC
MAX22666FAWE+/V*	6/0	200	Low	5	-40°C to +125°C	16-WSOIC

*Future product − contact Analog Devices for availability.

+Denotes a lead (Pb)–free/RoHS-compliant package.

/V Denotes an automotive qualified part.

Chip Information

PROCESS: BiCMOS

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	12/22	Release for Market Intro	—
1	9/23	Removed future product designation from MAX22666CAWE+ in the Ordering Information section	26

**ANALOG
DEVICES**

w w w . a n a l o g . c o m